

High Efficiency Thyristor

$$V_{RRM} = 1200V$$

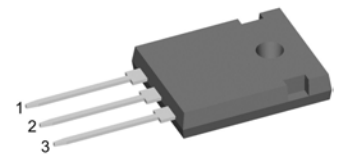
$$I_{TAV} = 20A$$

$$V_T = 1,3V$$

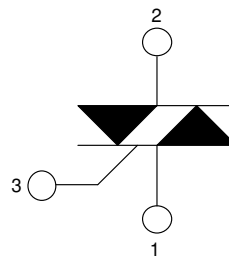
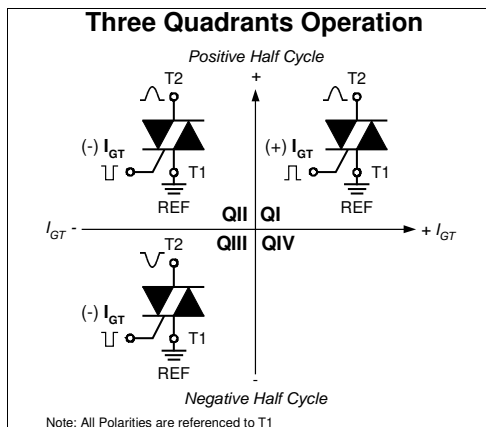
Three Quadrants operation: QI - QIII
 1~ Triac

Part number

CLA40MT1200NHR



Backside: isolated



Features / Advantages:

- Triac for line frequency
- Three Quadrants Operation
 - QI - QIII
- Planar passivated chip
- Long-term stability of blocking currents and voltages

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter
- AC power control
- Lighting and temperature control

Package: ISO247

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

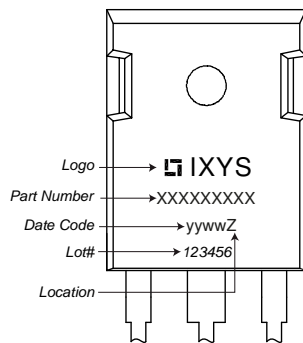
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Thyristor			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$V_{RSM/DSM}$	max. non-repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V
$V_{RRM/DRM}$	max. repetitive reverse/forward blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I_{RD}	reverse current, drain current	$V_{R/D} = 1200 V$	$T_{VJ} = 25^{\circ}C$		50	μA
		$V_{R/D} = 1200 V$	$T_{VJ} = 125^{\circ}C$		1	mA
V_T	forward voltage drop	$I_T = 20 A$	$T_{VJ} = 25^{\circ}C$		1,31	V
		$I_T = 40 A$			1,63	V
		$I_T = 20 A$	$T_{VJ} = 125^{\circ}C$		1,30	V
		$I_T = 40 A$			1,71	V
I_{TAV}	average forward current	$T_C = 100^{\circ}C$	$T_{VJ} = 150^{\circ}C$		20	A
I_{RMS}	RMS forward current per phase	180° sine			31	A
V_{T0}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0,86	V
r_T	slope resistance				21,4	m Ω
R_{thJC}	thermal resistance junction to case				1,2	K/W
R_{thCH}	thermal resistance case to heatsink			0,25		K/W
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		105	W
I_{TSM}	max. forward surge current	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		180	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		195	A
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		155	A
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		165	A
I^2t	value for fusing	$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 45^{\circ}C$		160	A ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		160	A ² s
		$t = 10 \text{ ms}; (50 \text{ Hz}), \text{ sine}$	$T_{VJ} = 150^{\circ}C$		120	A ² s
		$t = 8,3 \text{ ms}; (60 \text{ Hz}), \text{ sine}$	$V_R = 0 V$		115	A ² s
C_J	junction capacitance	$V_R = 230V \quad f = 1 \text{ MHz}$	$T_{VJ} = 25^{\circ}C$		9	pF
P_{GM}	max. gate power dissipation	$t_p = 30 \mu s$	$T_C = 150^{\circ}C$		5	W
		$t_p = 300 \mu s$			2,5	W
P_{GAV}	average gate power dissipation				0,5	W
$(di/dt)_{cr}$	critical rate of rise of current	$T_{VJ} = 150^{\circ}C; f = 50 \text{ Hz}$ repetitive, $I_T = 60 A$			150	A/ μs
		$t_p = 200 \mu s; di_G/dt = 0,15 A/\mu s;$ $I_G = 0,15A; V_D = \frac{2}{3} V_{DRM}$ non-repet., $I_T = 20 A$			500	A/ μs
$(dv/dt)_{cr}$	critical rate of rise of voltage	$V_D = \frac{2}{3} V_{DRM}$ $R_{GK} = \infty; \text{ method 1 (linear voltage rise)}$	$T_{VJ} = 150^{\circ}C$		500	V/ μs
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		1,5	V
			$T_{VJ} = -40^{\circ}C$		2,5	V
I_{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$		± 60	mA
			$T_{VJ} = -40^{\circ}C$		± 100	mA
V_{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 150^{\circ}C$		0,2	V
I_{GD}	gate non-trigger current				± 3	mA
I_L	latching current	$t_p = 10 \mu s$	$T_{VJ} = 25^{\circ}C$		75	mA
		$I_G = 0,1A; di_G/dt = 0,1 A/\mu s$				
I_H	holding current	$V_D = 6 V \quad R_{GK} = \infty$	$T_{VJ} = 25^{\circ}C$		50	mA
t_{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25^{\circ}C$		2	μs
		$I_G = 0,1A; di_G/dt = 0,1 A/\mu s$				
t_q	turn-off time	$V_R = 100 V; I_T = 20A; V_D = \frac{2}{3} V_{DRM}$ $di/dt = 10 A/\mu s; dv/dt = 20 V/\mu s; t_p = 200 \mu s$	$T_{VJ} = 125^{\circ}C$		150	μs

Package ISO247		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			50	A
T_{VJ}	virtual junction temperature		-55		150	°C
T_{op}	operation temperature		-55		125	°C
T_{stg}	storage temperature		-55		150	°C
Weight				6		g
M_D	mounting torque		0,8		1,2	Nm
F_C	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	2,7			mm
$d_{Spb/Apb}$		terminal to backside	4,1			mm
V_{ISOL}	isolation voltage	t = 1 second	3600			V
		t = 1 minute	3000			V

Product Marking



Part description

C = Thyristor (SCR)
 L = High Efficiency Thyristor
 A = (up to 1200V)
 40 = Current Rating [A]
 MT = 1~ Triac
 1200 = Reverse Voltage [V]
 N = Three Quadrants operation: QI - QIII
 HR = ISO247 (3)

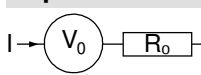
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	CLA40MT1200NHR	CLA40MT1200NHR	Tube	30	521685

Similar Part	Package	Voltage class
CLA60MT1200NHR	ISO247 (3)	1200
CLA80MT1200NHR	ISO247 (3)	1200

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}\text{C}$



Thyristor

$V_{0\ max}$	threshold voltage	0,86	V
$R_{0\ max}$	slope resistance *	18,9	mΩ

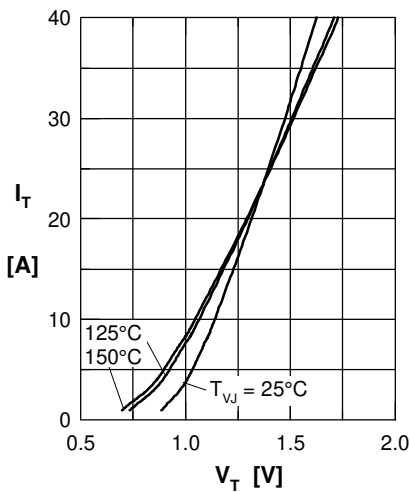
Thyristor


Fig. 1 Forward characteristics

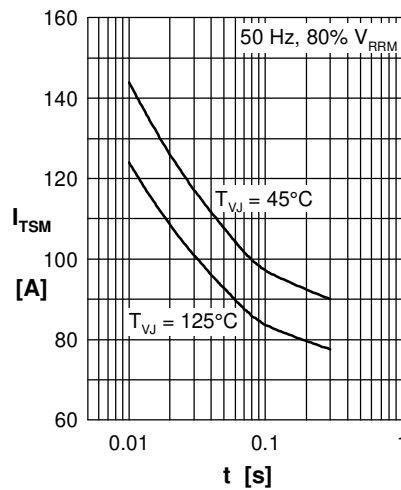


Fig. 2 Surge overload current

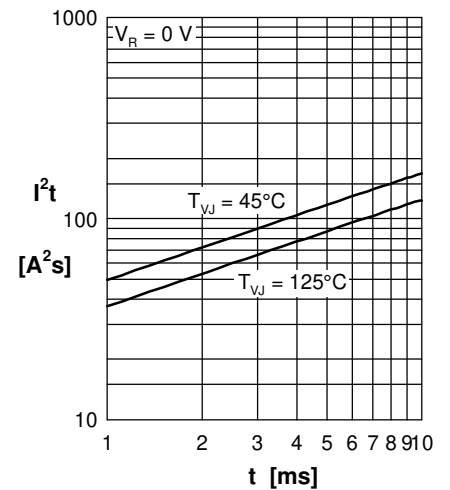
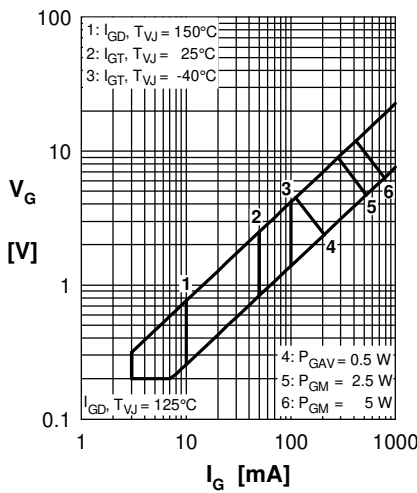

 Fig. 3 I^2t versus time (1-10 ms)


Fig. 4 Gate trigger characteristics

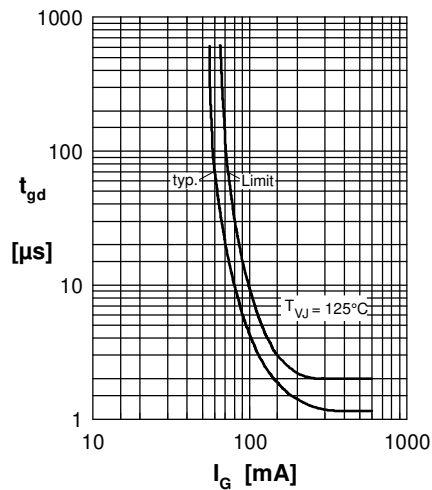


Fig. 5 Gate controlled delay time

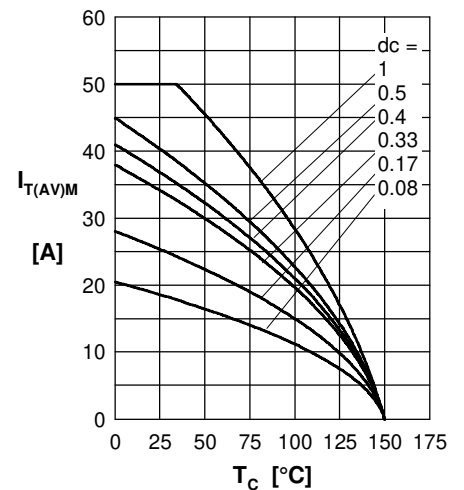


Fig. 6 Max. forward current at case temperature

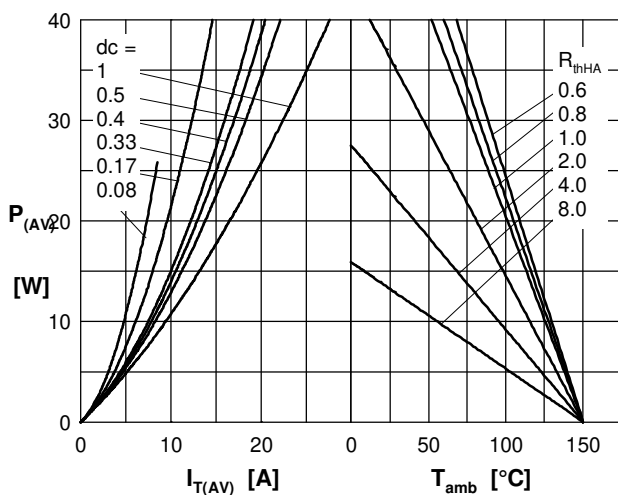
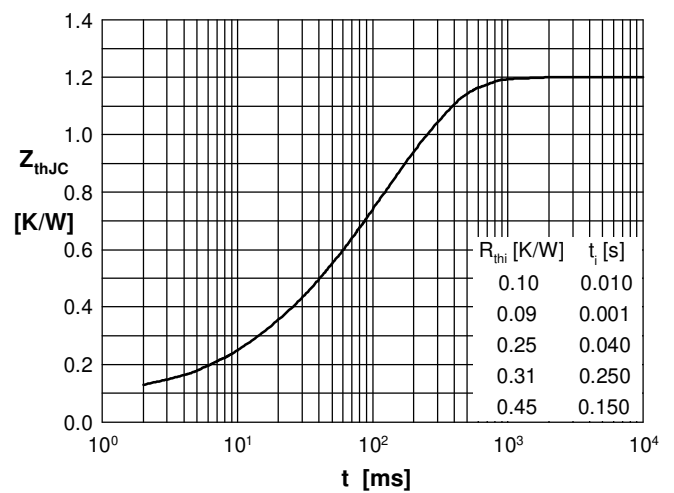

 Fig. 7a Power dissipation versus direct output current
 Fig. 7b and ambient temperature


Fig. 8 Transient thermal impedance junction to case